

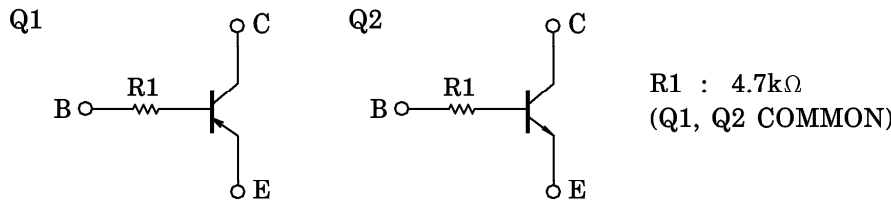
TOSHIBA TRANSISTOR
 SILICON PNP EPITAXIAL TYPE (PCT PROCESS) SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

RN4610

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT
 AND DRIVER CIRCUIT APPLICATIONS.

- Including Two Devices in SM6 (Super Mini Type with 6 leads)
- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process

EQUIVALENT CIRCUIT



Q1 MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA

Q2 MAXIMUM RATINGS (Ta = 25°C)

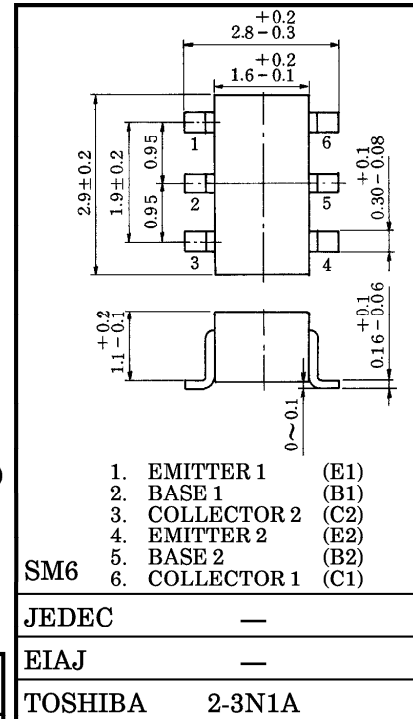
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	100	mA

Q1, Q2 COMMON MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P _C *	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

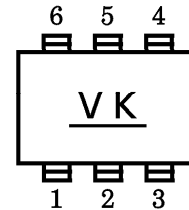
* : Total Rating

Unit in mm

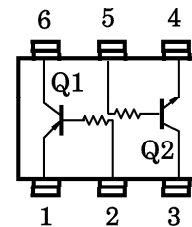


Weight : 0.015g

MARKING



EQUIVALENT CIRCUIT (TOP VIEW)



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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

Q1 ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -1mA$	120	—	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -5mA, I_B = -0.25mA$	—	-0.1	-0.3	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3	6	pF

Q2 ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 50V, I_E = 0$	—	—	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	100	nA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 1mA$	120	—	700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5mA, I_B = 0.25mA$	—	0.1	0.3	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 5mA$	—	250	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3	6	pF

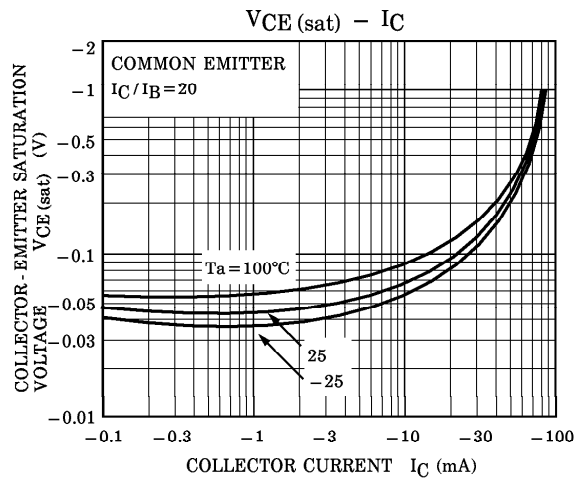
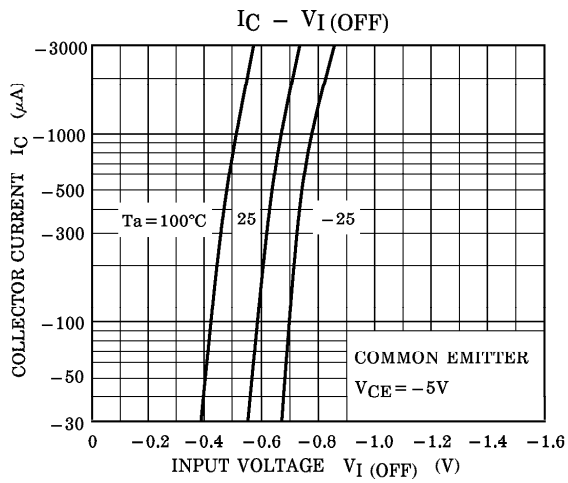
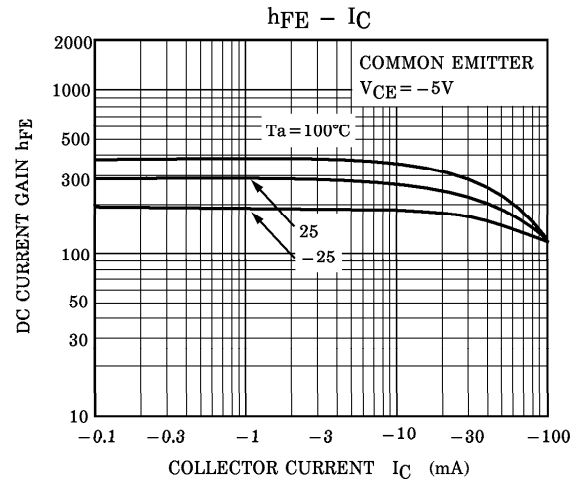
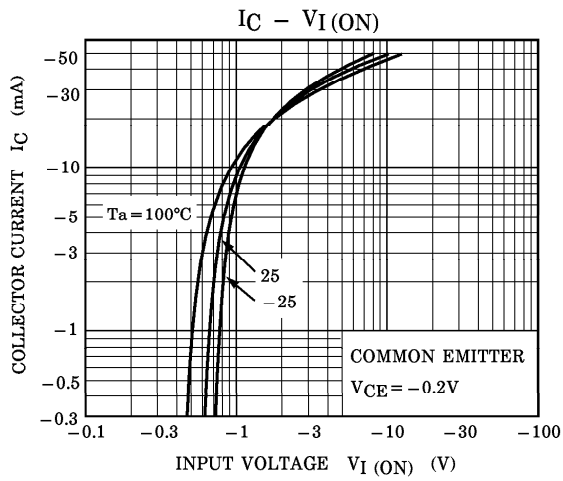
Q1, Q2 COMMON ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Resistor	R1	—	3.29	4.7	6.11	kΩ

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Q1



Q2

